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### AMENDMENTS TO THE CLAIMS

#### Listing of Claims:

1. **(Previously presented)** A semiconductor processing apparatus comprising a reaction chamber and one or more vitreous components that have a support surface for supporting other components in the reaction chamber, said support surface being covered at least in part by a devitrification barrier coating that is bonded to said support surface and directly contacts said supported other components in the reaction chamber; where said devitrification barrier coating has a thickness between about 1 and 10,000 angstroms.

2. **(Original)** The apparatus of Claim 1, wherein said one or more vitreous components are formed from quartz.

3. **(Original)** The apparatus of Claim 1, wherein said devitrification barrier comprises silicon nitride.

4. **(Original)** The apparatus of Claim 1, wherein said devitrification barrier coating is formed from silicon nitride that has been deposited on said one or more vitreous components using CVD deposition.

5. **(Canceled)**

6. **(Previously presented)** The apparatus of Claim 1, where said devitrification barrier coating has a thickness between about 50 and 5000 angstroms.

7. **(Previously presented)** The apparatus of Claim 6, where said devitrification barrier coating has a thickness between about 500 and 3,000 angstroms.

8. **(Previously presented)** The apparatus of Claim 7, where said devitrification barrier coating has a thickness of about 800 angstroms.

9. **(Previously presented)** The apparatus of Claim 1, where said devitrification barrier coating is selected from the group consisting of silicon nitride, diamond, titanium nitride, titanium carbon nitride, and combinations thereof.

10. **(Previously presented)** The apparatus of Claim 1, wherein said devitrification barrier coating covers an entire portion of said support surface of said one or more vitreous components.

11. **(Canceled)**